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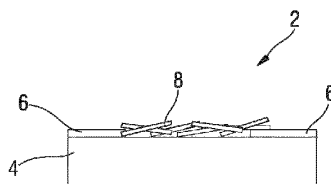
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(54) Title: GAS SENSOR DEVICE WITH HIGH SENSITIVITY AT LOW TEMPERATURE AND METHOD OF FABRICATION THEREOF

FIG 2



(57) Abstract: The invention is directed to a method for producing a gas sensor (2) comprising a step of providing a substrate (4) with two coplanar electrodes (6) and a step of forming a ZnO nanowires network (8) on said two electrodes (6). The step of forming a ZnO nanowires network (8) on said two electrodes (6) is performed as follows: synthesizing ZnO nanowires with a liquid phase sequential growth method; dispersing said synthesized nanowires in a solvent; drop casting the solution containing the solvent and the ZnO nanowires on the electrodes; drying the solution at a temperature inferior to 85°C. The invention is also directed to a gas sensor working at low temperature such as room temperature.

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